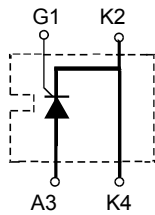
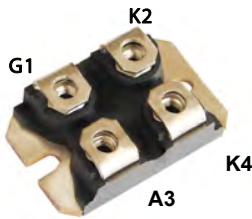
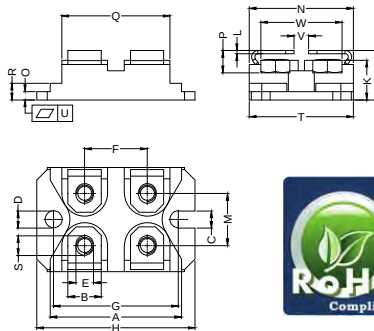


STO150GK08S

Single Thyristor Modules



Dimensions SOT-227



Dim.	Millimeter		Dim.	Millimeter	
	Min.	Max.		Min.	Max.
A	31.30	31.62	M	12.20	14.00
B	7.80	8.20	N	25.15	25.62
C	4.09	4.29	O	1.98	2.13
D	4.09	4.29	P	4.15	4.62
E	4.09	4.29	Q	25.90	26.30
F	14.91	15.11	R	3.94	4.42
G	30.12	30.30	S	4.45	4.85
H	38.20	38.56	T	24.59	25.07
J	12.30	12.90	U	0.05	0.10
K	8.92	9.60	V	3.00	4.80
L	0.76	0.84	W	19.81	21.08



Type	V _{RSM} V _{D_{SM}} V	V _{RRM} V _{D_{RM}} V
STO150GK08S	900	800

Symbol	Test Conditions		Maximum Ratings	Unit
I _{TRMS}	T _{VJ} = T _{VJM}		235	A
I _{TAVM}	T _C = 80°C; (180° sine)		150	
I _{TSM}	T _{VJ} = 45°C V _R = 0	t = 10ms (50Hz), sine t = 8.3ms (60Hz), sine	2000 2150	A
	T _{VJ} = T _{VJM} V _R = 0	t = 10ms (50Hz), sine t = 8.3ms (60Hz), sine	1750 1850	
I ² _t	T _{VJ} = 45°C V _R = 0	t = 10ms (50Hz), sine t = 8.3ms (60Hz), sine	20000 19400	A ² s
	T _{VJ} = T _{VJM} V _R = 0	t = 10ms (50Hz), sine t = 8.3ms (60Hz), sine	15300 14400	
(di/dt) _{cr}	T _{VJ} = T _{VJM} f = 50Hz, t _p = 200us V _D = 2/3 V _{DRM} I _G = 0.3A di _G /dt = 0.3A/us	repetitive, I _T = 150A	150	A/us
		non repetitive, I _T = I _{TAVM}	500	
(dv/dt) _{cr}	T _{VJ} = T _{VJM} ; R _{GK} = ∞; method 1 (linear voltage rise)	V _{DR} = 2/3 V _{DRM}	1000	V/us
P _{GM} P _{GAVM}	T _{VJ} = T _{VJM} I _T = I _{TAVM}	t _p = 30us t _p = 300us	10 5 0.5	W
V _{RGM}			10	
T _{VJ} T _{VJM} T _{stg}			-40...+150 150 -40...+125	°C
V _{ISOL}	50/60Hz, RMS I _{ISOL} ≤ 1mA		2500	V~
M _d	Mounting torque (M4) Terminal connection torque (M4)		1.1-1.5/9-13 1.1-1.5/9-13	Nm/lb.in.
Weight	typical		30	g

Sirectifier®

STO150GK08S

Single Thyristor Modules

Symbol	Test Conditions	Characteristic Values	Unit
I_R, I_D	$T_{VJ}=T_{VJM}; V_R=V_{RRM}; V_D=V_{DRM}$	≤ 10	mA
V_T	$I_T=450A; T_{VJ}=25^{\circ}C$	≤ 1.45	V
V_{TO}	For power-loss calculations only	≤ 0.80	V
r_T		≤ 3.8	m Ω
V_{GT}	$V_D=6V; T_{VJ}=25^{\circ}C$ $T_{VJ}=-40^{\circ}C$	≤ 1.5 ≤ 1.6	V
I_{GT}	$V_D=6V; T_{VJ}=25^{\circ}C$ $T_{VJ}=-40^{\circ}C$	≤ 150 ≤ 200	mA
V_{GD}	$T_{VJ}=T_{VJM}; V_D=2/3V_{DRM}$	≤ 0.2	V
I_{GD}		≤ 5	mA
I_L	$T_{VJ}=25^{\circ}C; t_p=10\mu s$ $I_G=0.3A; di/dt=0.3A/\mu s$	≤ 450	
I_H	$T_{VJ}=25^{\circ}C; V_D=6V; R_{GK}=\infty$	≤ 200	
t_{gd}	$T_{VJ}=25^{\circ}C; V_D=1/2V_{DRM}$ $I_G=0.3A; di/dt=0.3A/\mu s$	≤ 2	μs
t_q	$T_{VJ}=T_{VJM}; I_T=20A; t_p=200\mu s; di/dt=-10A/\mu s$ typ. $V_R=100V; dv/dt=15V/\mu s; V_D=2/3V_{DRM}$	≤ 150	
R_{thJC}	DC current	≤ 0.20	K/W
R_{thCH}	DC current	≤ 0.10	
d_s	Creeping distance on surface	≤ 8	mm
d_A	Creepage distance in air	≤ 4	
a	Max. allowable acceleration	≤ 50	m/s ²

FEATURES

- *Thyristor controller for AC for mains frequency
- *International standard package SOT-227B (ISOTOP compatible)
- *Isolation voltage 2500V~
- *Glass passivated chips
- *UL File NO. E310749
- *RoHS compliant

APPLICATIONS

- *Switching and control of single and three phase AC Softstart
- *AC motor controller
- *Solid states switches
- *Light and temperature control

ADVANTAGES

- *Easy to mount with two screws
- *Space and weight savings
- *Improved temperature and power cycling
- *High power density

STO150GK08S

Single Thyristor Modules

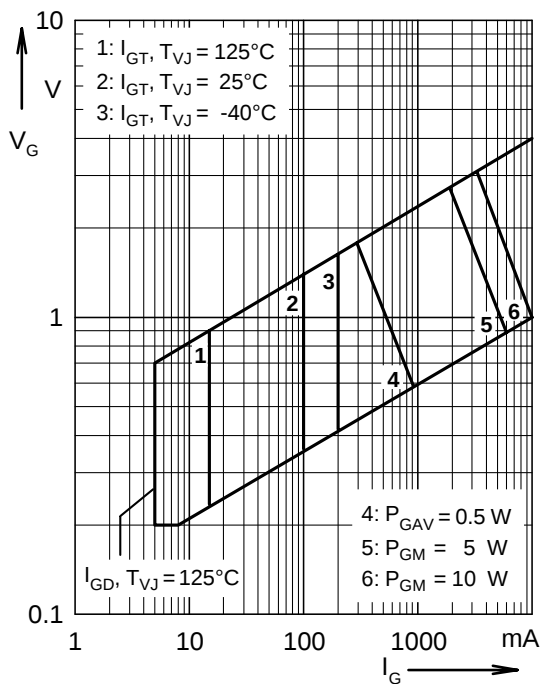


Fig. 1 Gate trigger characteristics

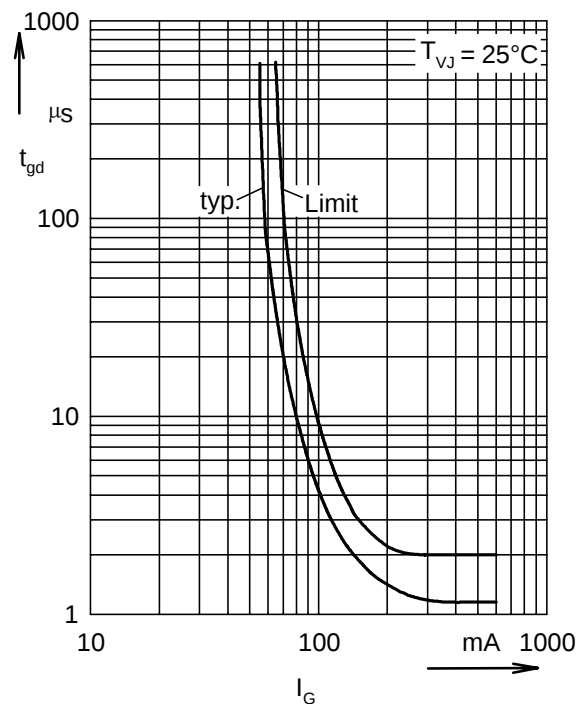


Fig. 2 Gate trigger delay time

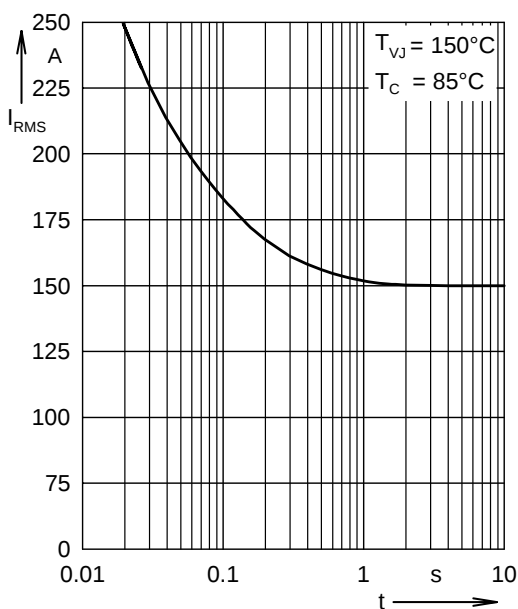


Fig.3 Rated RMS current versus time (360° conduction)

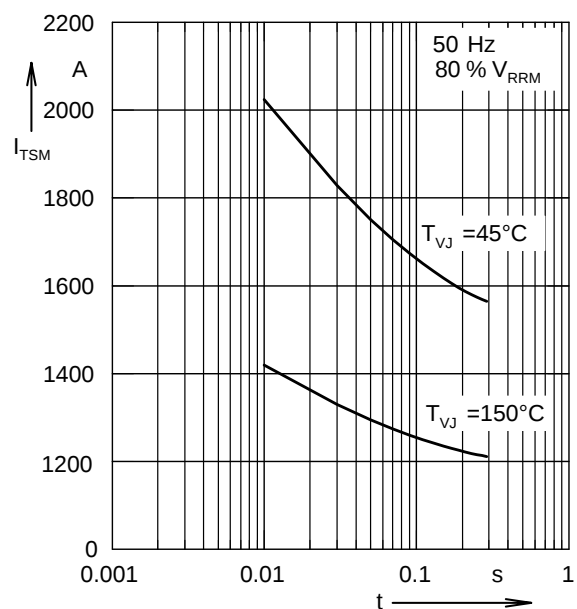


Fig.4 Surge overload current